

Silicon PNP Power Transistors

2SB511

DESCRIPTION

- With TO-220C package
- Complement to type 2SD325
- Low collector saturation voltage

APPLICATIONS

- Designed for use in low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

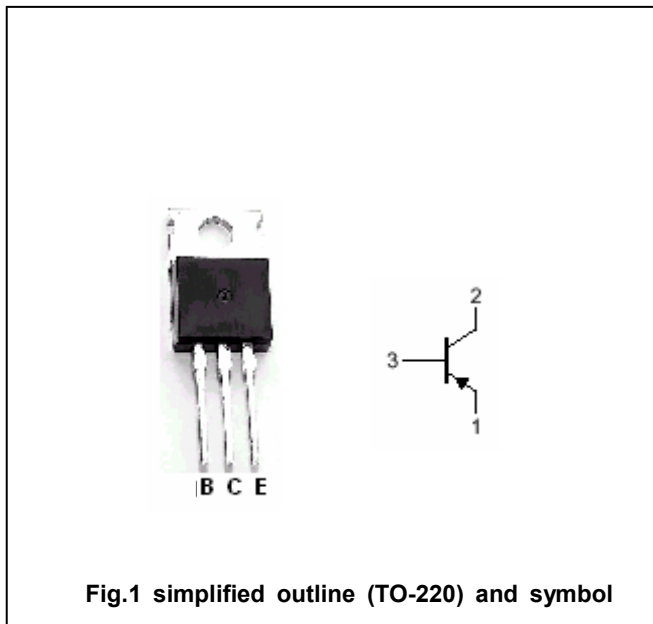


Fig.1 simplified outline (TO-220) and symbol

Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	-35	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	-35	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-5	V
I <sub>C</sub>	Collector current (DC)		-1.5	A
I <sub>CM</sub>	Collector current -peak		-3.0	A
P <sub>C</sub>	Collector dissipation	T <sub>a</sub> =25°C	1.75	W
		T <sub>C</sub> =25°C	10	
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-50~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-10mA; I <sub>B</sub> =0	-35			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-1.5A; I <sub>B</sub> =-0.15A			-1.0	V
V <sub>BE</sub>	Base-emitter on voltage	I <sub>C</sub> =-1A; V <sub>CE</sub> =-5V			-1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-20V; I <sub>E</sub> =0			-0.1	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-5V; I <sub>C</sub> =0			-0.1	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =-1A; V <sub>CE</sub> =-2V	40		320	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =-0.1A; V <sub>CE</sub> =-2V	35			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-0.5A; V <sub>CE</sub> =-5V		8		MHz

◆ h<sub>FE-1</sub> Classifications

C	D	E	F
40-80	60-120	100-200	160-320

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PACKAGE OUTLINE

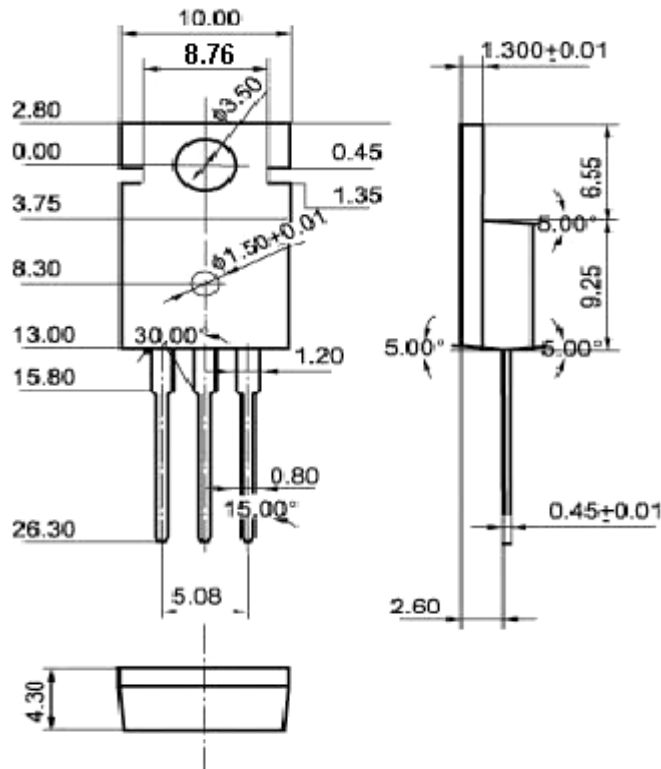


Fig.2 Outline dimensions (unindicated tolerance:  $\pm 0.10\text{mm}$ )